



# FP102

PNP Epitaxial Planar Silicon Transistor/  
Composite Schottky Barrier Diode

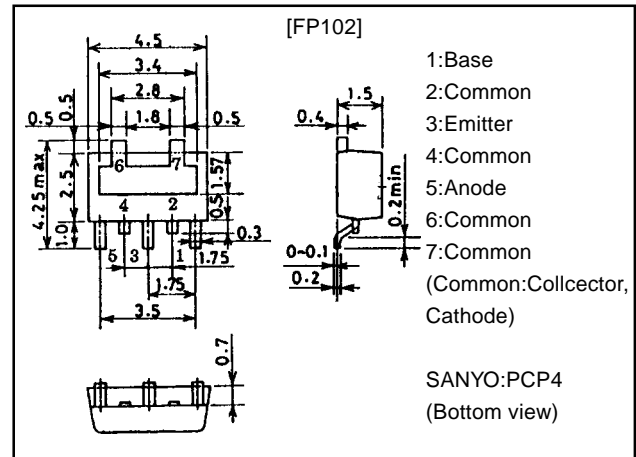
## DC-DC Converter Applications

### Features

- Composite type with a PNP transistor and a Schottky barrier diode contained in one package, facilitating high-density mounting.
- The FP102 is formed with 2chips, one being equivalent to the 2SB1396 and the other the SB07-03C, placed in one package.

### Package Dimensions

unit:mm  
2088A



### Specifications

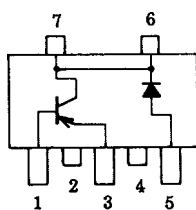
#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
[TR]				
Collector-to-Base Voltage	$V_{CB0}$		-15	V
Collector-to-Emitter Voltage	$V_{CE0}$		-11	V
Emitter-to-Base Voltage	$V_{EB0}$		-7	V
Collector Current	$I_C$		-3	A
Collector Current (Pulse)	$I_{CP}$		-5	A
Base Current	$I_B$		-600	mA
Collector Dissipation	$P_C$	Mounted on ceramic board (250mm <sup>2</sup> ×0.8mm)	1.3	W
Junction Temperature	$T_J$		150	°C
[SBD]				
Repetitive Peak Reverse Voltage	$V_{RRM}$		30	V
Non-repetitive Peak Reverse Surge Voltage	$V_{RSM}$		35	V
Average Rectified Current	$I_O$		700	mA
Surge Forward Current	$I_{FSM}$	50Hz sine wave, 1cycle	5	A
Junction Temperature	$T_J$		-55 to +125	°C
Storage Temperature	$T_{stg}$		-55 to +125	°C

Marking: 102

Continued on next page.

### Electrical Connection



- 1:Base  
2:Common  
3:Emitter  
4:Common  
5:Anode  
6:Common  
7:Common  
(Common:Collector, Cathode)  
(Top view)

# FP102

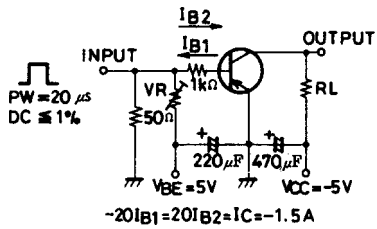
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## Electrical Characteristics at Ta=25°C

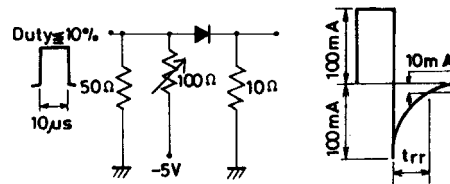
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[TR]						
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=-12V, I_E=0$			-0.1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=-6V, I_C=0$			-0.1	$\mu A$
DC Current Gain	$h_{FE1}$	$V_{CE}=-2V, I_C=-0.5A$	140		560	
	$h_{FE2}$	$V_{CE}=-2V, I_C=-3A$	70			
Gain-Bandwidth Product	$f_T$	$V_{CE}=-2V, I_C=-0.3A$		400		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=-10V, f=1MHz$		26		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=-1.5A, I_B=-30mA$		-0.22	-0.4	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=-1.5A, I_B=-30mA$		-0.9	-1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-15			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1mA, R_{BE}=\infty$	-11			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-7			V
Turn-ON Time	$t_{on}$	See specified Test Circuit		25		ns
Storage Time	$t_{stg}$	See specified Test Circuit		200		ns
Fall Time	$t_f$	See specified Test Circuit		10		ns
[SBD]						
Reverse Voltage	$V_R$	$I_R=300\mu A$	30			V
Forward Voltage	$V_F$	$I_F=700mA$			0.55	V
Reverse Current	$I_R$	$V_R=15V$			80	$\mu A$
Interterminal Capacitance	$C$	$V_R=10V, f=1MHz$		28		pF
Reverse Recovery Time	$t_{rr}$	$I_F=I_R=100mA$ , See specified Test Circuit			10	ns
Thermal Resistance	$R_{thj-a}$	Mounted on ceramic board (250mm <sup>2</sup> ×0.8mm)		120		°C/W

## Switching Time Test Circuit

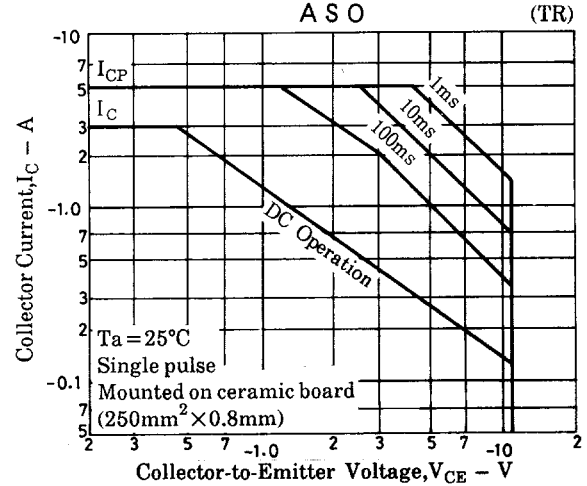
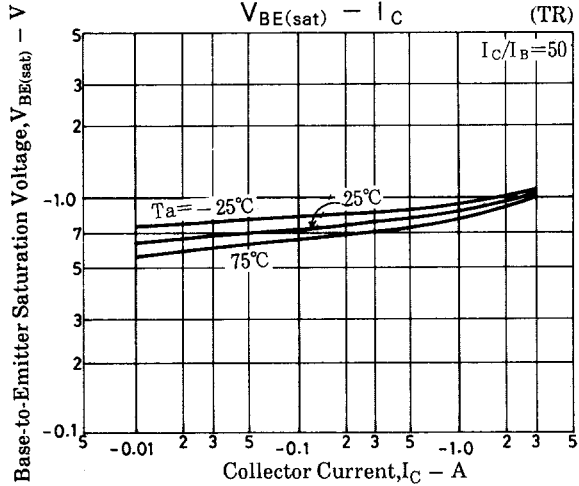
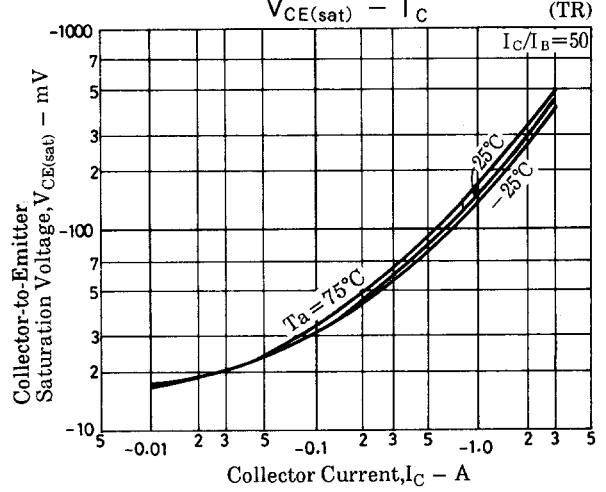
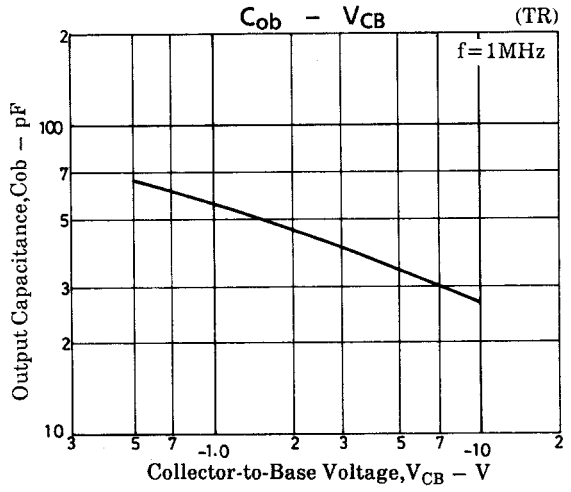
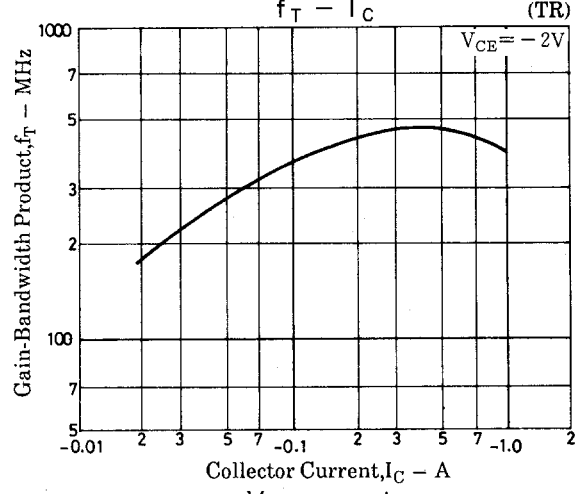
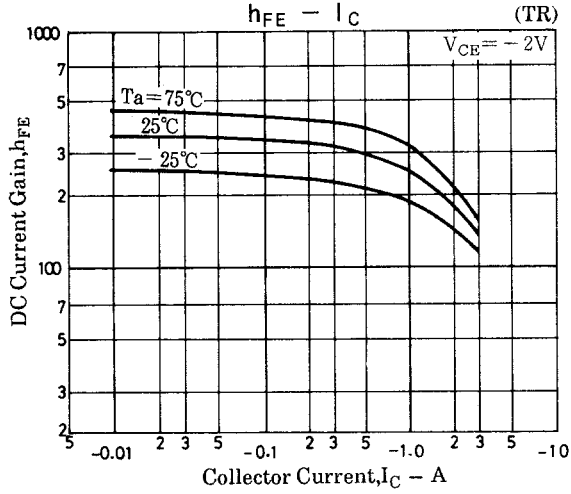
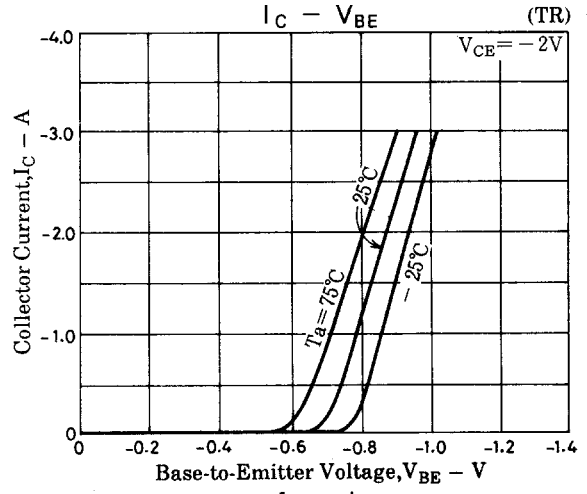
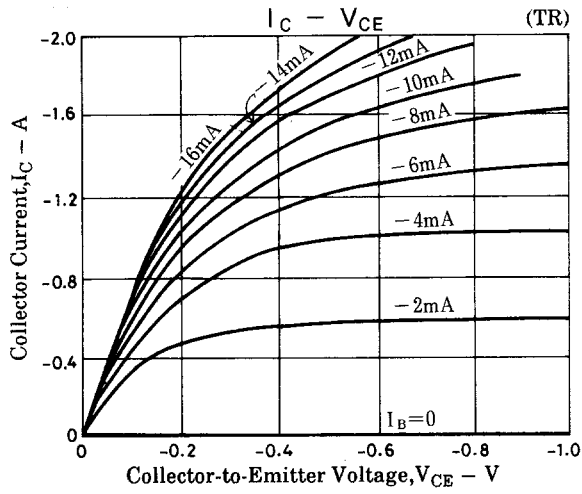
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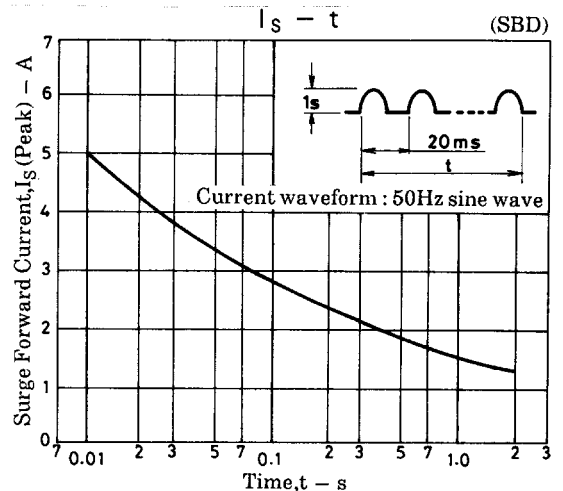
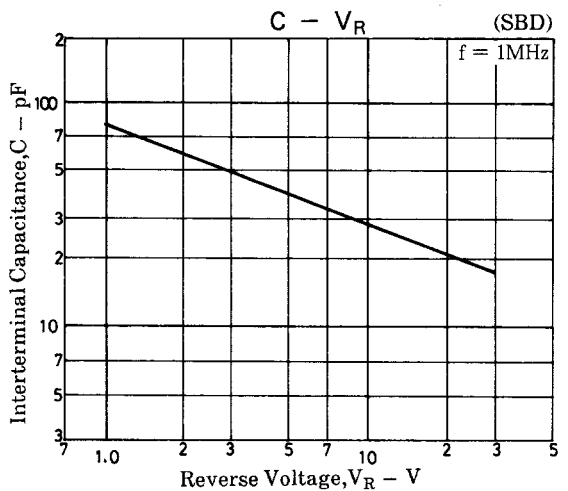
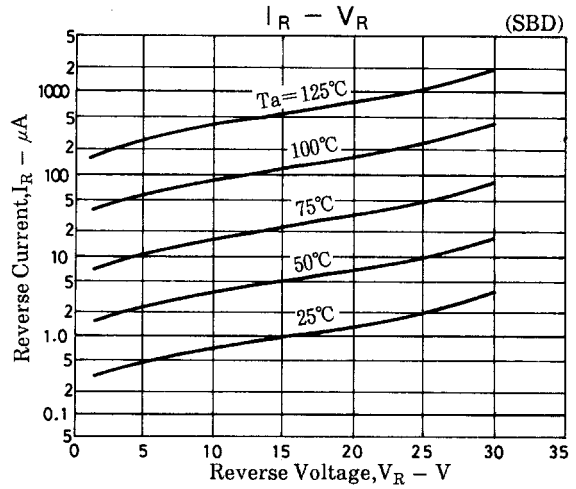
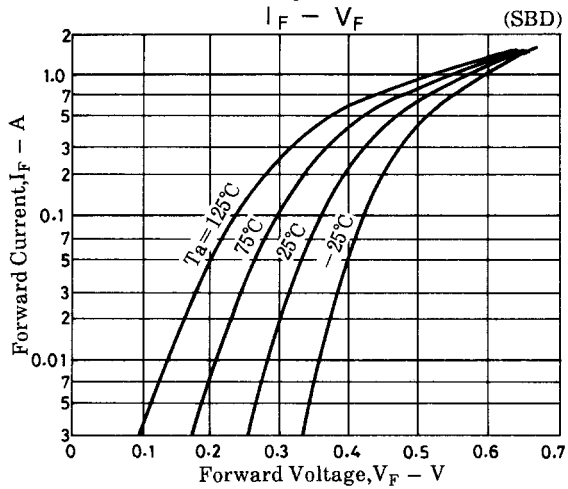
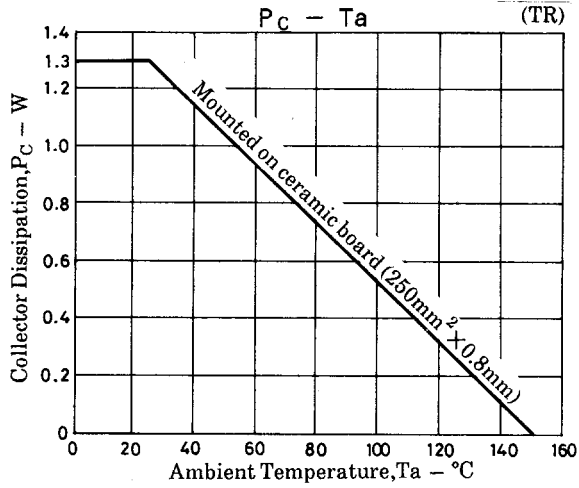


(SBD)



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